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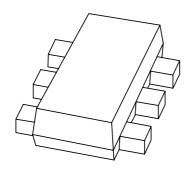
If you have any questions related to the data sheet, please contact our nearest sales office via e-mail or telephone (details via **salesaddresses@nexperia.com**). Thank you for your cooperation and understanding,

Kind regards,

Team Nexperia

DISCRETE SEMICONDUCTORS

DATA SHEET



PMEG1020EVUltra low V_F MEGA Schottky barrier rectifier

Product data sheet 2003 Jul 15



Ultra low V_F MEGA Schottky barrier rectifier

PMEG1020EV

FEATURES

Forward current: 2 AReverse voltage: 10 VUltra low forward voltage

· Ultra small plastic SMD package.

APPLICATIONS

Low voltage rectification

• High efficiency DC/DC conversion

• Switch mode power supply

· Inverse polarity protection

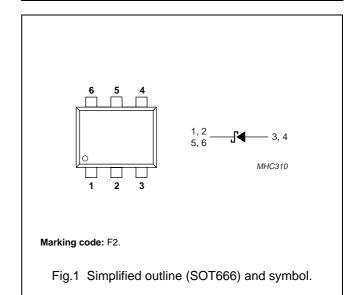
· Low power consumption applications.

DESCRIPTION

Planar Maximum Efficiency General Application (MEGA) Schottky barrier rectifier with an integrated guard ring for stress protection encapsulated in a SOT666 ultra small plastic SMD package.

PINNING

PIN	DESCRIPTION
1	cathode
2	cathode
3	anode
4	anode
5	cathode
6	cathode



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_R	continuous reverse voltage		_	10	V
I _F	continuous forward current	T _{sp} ≤ 55 °C; note 1	_	2	А
I _{FRM}	repetitive peak forward current	$t_p \le 1$ ms; $\delta \le 0.5$; note 1	_	3.2	А
I _{FSM}	non-repetitive peak forward current	t _p = 8 ms square wave; note 1	_	9	А
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		_	150	°C
T _{amb}	operating ambient temperature		-65	+150	°C

Note

1. Only valid if pins 3 and 4 are connected in parallel.

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ELECTRICAL CHARACTERISTICS

 T_{amb} = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
V _F	forward voltage	see Fig.2; note 1			
		I _F = 0.01 A	100	130	mV
		I _F = 0.1 A	164	200	mV
		I _F = 1 A	255	350	mV
		I _F = 2 A	306	460	mV
I_R	reverse current	see Fig.3 note 2			
		V _R = 5 V	0.7	2	mA
		V _R = 8 V	1	2.5	mA
		V _R = 10 V	1.2	3	mA
C _d	diode capacitance	$V_R = 5 \text{ V}$; f = 1 MHz; see Fig.4	37	45	pF

Notes

- 1. Pulse test: $t_p = 300 \ \mu s$; $\delta = 0.02$.
- For Schottky barrier rectifiers thermal runaway has to be considered, as in some applications the reverse power losses (P_R) are a significant part of the total power losses.

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-a}	thermal resistance from junction to ambient	note 1	405	K/W
		note 2	215	K/W
R _{th j-s}	thermal resistance from junction to solder point	note 3	80	K/W

Notes

- 1. Refer to SOT666 standard mounting conditions.
- 2. Device mounted on a printed-circuit board, single-sided copper, tinplated, mounting pad for cathode 1 cm².
- 3. Solder point of cathode tabs.

Soldering

Reflow soldering is the only recommended soldering method.

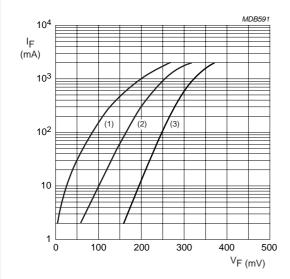
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Product data sheet **NXP Semiconductors**

Ultra low V_F MEGA Schottky barrier rectifier

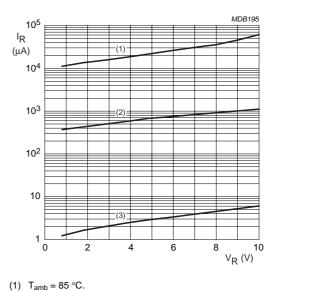
PMEG1020EV

GRAPHICAL DATA



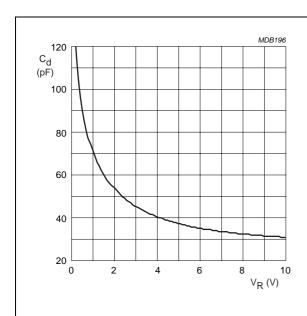
- (1) $T_{amb} = 85 \, ^{\circ}C$.
- (2) $T_{amb} = 25 \, ^{\circ}C$.
- (3) $T_{amb} = -40 \, ^{\circ}C$.

Fig.2 Forward current as a function of forward voltage; typical values.



- (2) $T_{amb} = 25 \, ^{\circ}C$.
- (3) $T_{amb} = -40 \, ^{\circ}C$.

Fig.3 Reverse current as a function of reverse voltage; typical values.



f = 1 MHz; $T_{amb} = 25 \,^{\circ}\text{C}$.

Fig.4 Diode capacitance as a function of reverse voltage; typical values.

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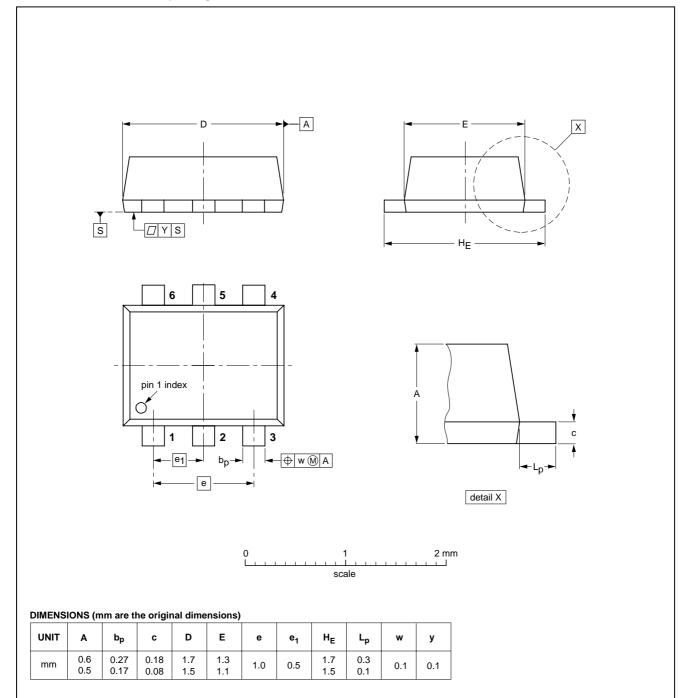
Ultra low V_F MEGA Schottky barrier rectifier

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PACKAGE OUTLINE

Plastic surface mounted package; 6 leads

SOT666



REFERENCES

EIAJ

JEDEC

EUROPEAN

PROJECTION

ISSUE DATE

01-01-04 01-08-27

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IEC

OUTLINE VERSION

SOT666

Ultra low V_F MEGA Schottky barrier rectifier

PMEG1020EV

DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

Notes

- 1. Please consult the most recently issued document before initiating or completing a design.
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Customer notification

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Contact information

For additional information please visit: http://www.nxp.com

For sales offices addresses send e-mail to: salesaddresses@nxp.com

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